

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1505S uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

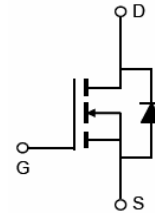
General Features

- $V_{DS} = 150V, I_D = 5.1A$
 $R_{DS(ON)} < 65m\Omega @ V_{GS}=10V$ (Typ: 55m Ω)
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature

Application

- DC/DC converters and Off-Line UPS
- High Voltage Synchronous Rectifier
- Hard switched and high frequency circuits
- Uninterruptible power supply

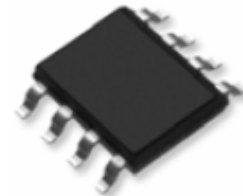
100% ΔV_d s TESTED!



Schematic diagram



Marking and pin assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1505S	NCEP1505S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	5.1	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	3.6	A
Pulsed Drain Current ^(Note 1)	I_{DM}	20	A
Single pulse avalanche energy ^(Note 5)	E_{AS}	60	mJ
Maximum Power Dissipation	$T_C = 25^\circ C$	5	W
	$T_A = 25^\circ C$	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	$^\circ C/W$
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	25	

Electrical Characteristics (T_A=25°C unless otherwise noted)

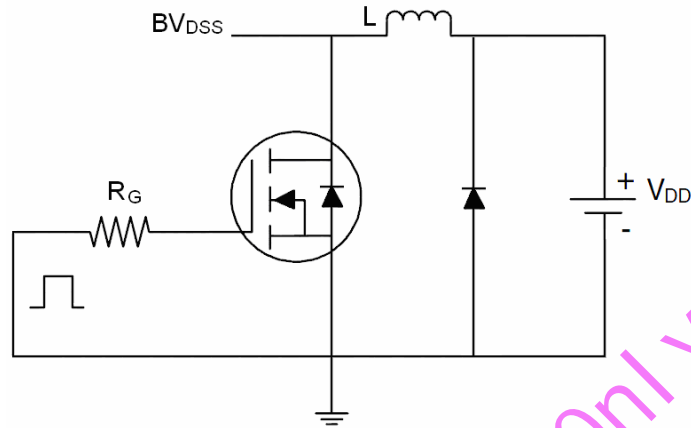
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5	3.3	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.1A	-	55	65	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5.1A	-	12.5	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{ISS}	V _{DS} =75V, V _{GS} =0V, F=1.0MHz	-	550	730	PF
Output Capacitance	C _{OSS}		-	62	80	PF
Reverse Transfer Capacitance	C _{RSS}		-	2.5	4.5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =75V, I _D =5.1A V _{GS} =10V, R _G =3Ω	-	7.5	14	nS
Turn-on Rise Time	t _r		-	1.4	8.5	nS
Turn-Off Delay Time	t _{d(off)}		-	12.5	21	nS
Turn-Off Fall Time	t _f		-	2.5	8	nS
Total Gate Charge	Q _g	V _{DS} =75V, I _D =5.1A, V _{GS} =10V	-	8.5	12	nC
Gate-Source Charge	Q _{gs}		-	2.8		nC
Gate-Drain Charge	Q _{gd}		-	1.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =5.1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	5.1	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	58	95	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note 3)	-	69	110	nC

Notes:

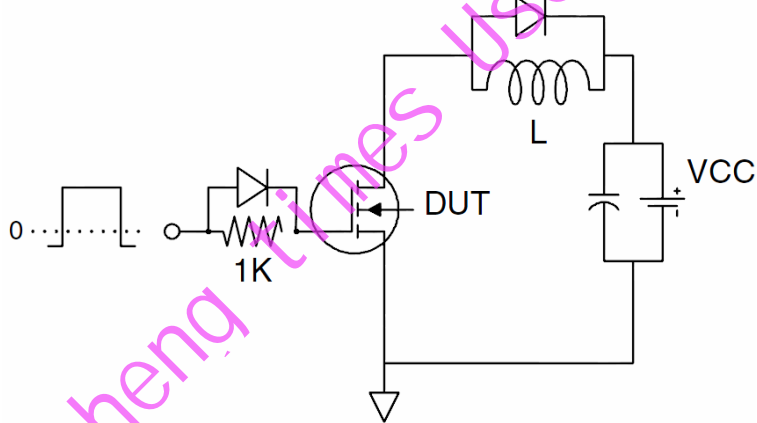
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

Test Circuit

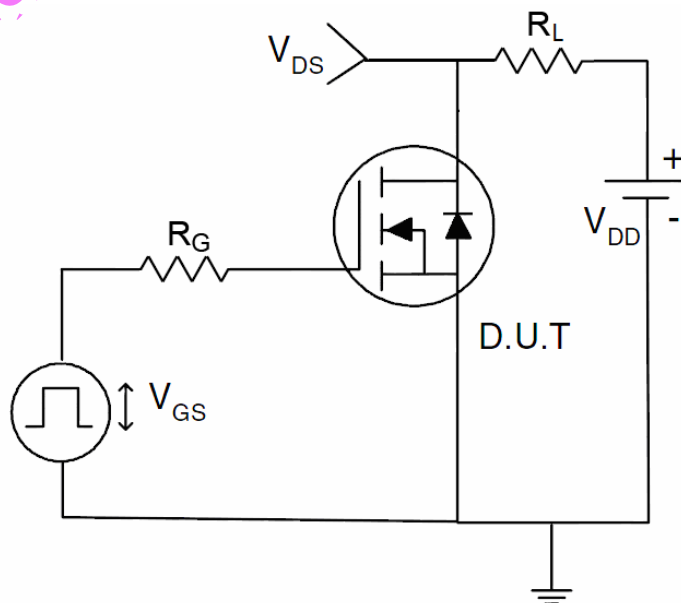
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

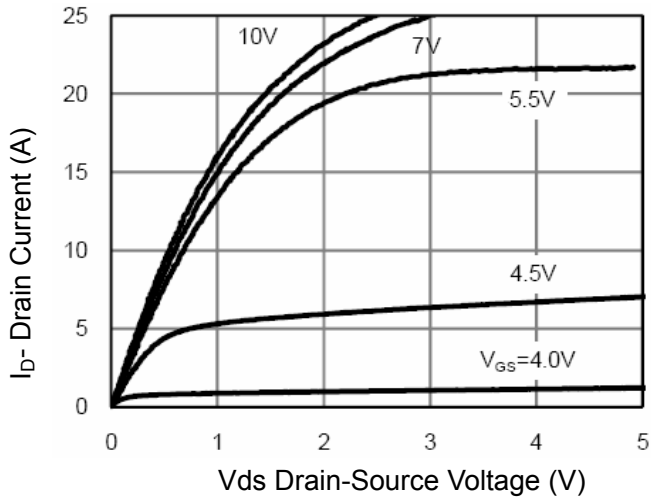


Figure 1 Output Characteristics

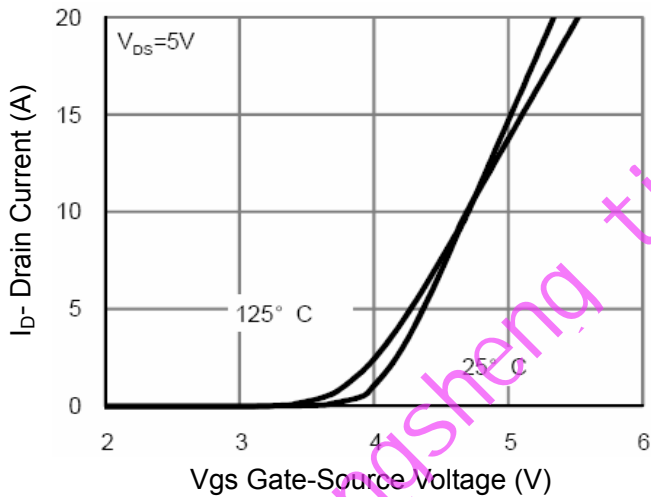


Figure 2 Transfer Characteristics

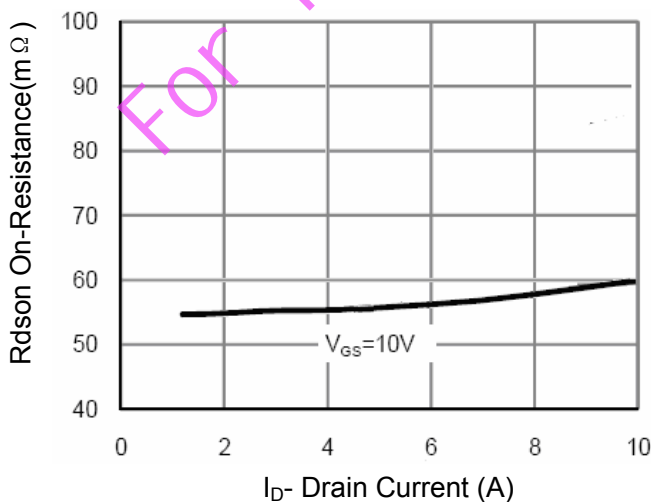


Figure 3 Rdson- Drain Current

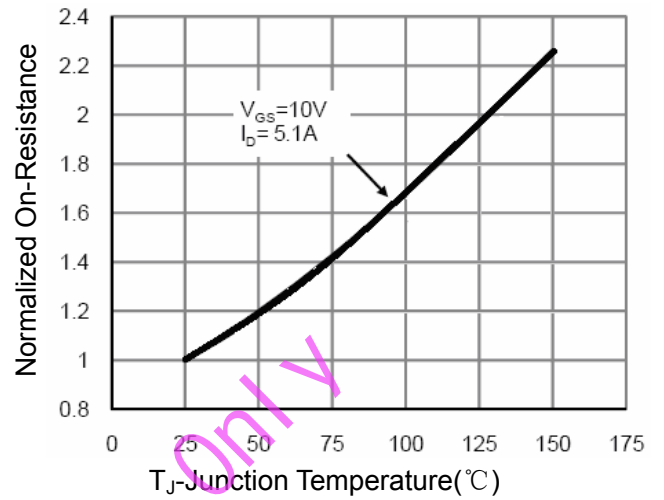


Figure 4 Rdson-Junction Temperature

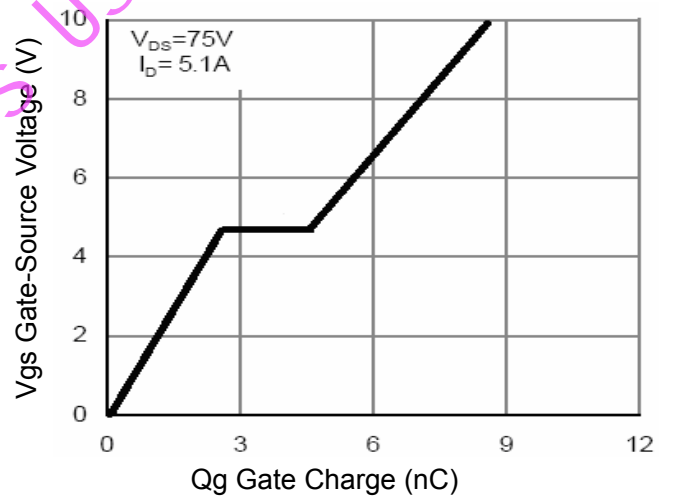


Figure 5 Gate Charge

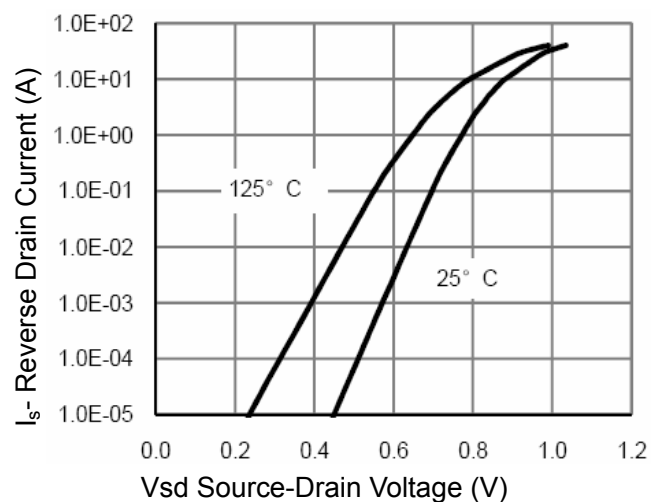


Figure 6 Source- Drain Diode Forward

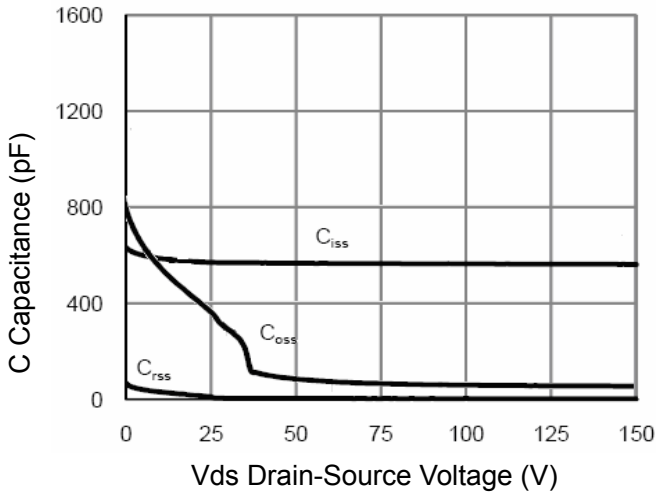


Figure 7 Capacitance vs Vds

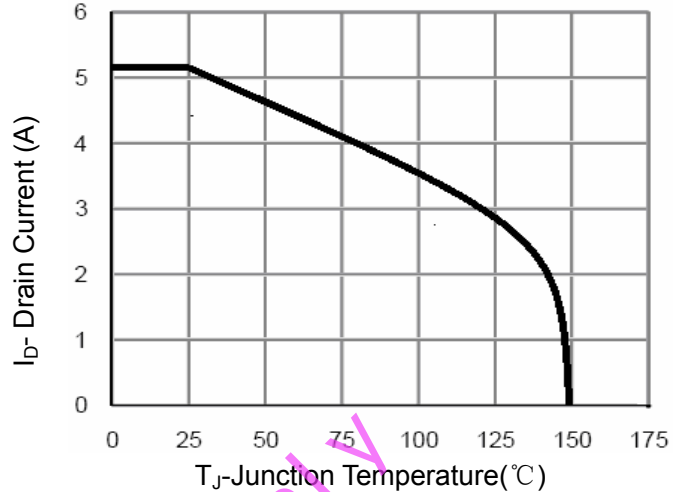


Figure 9 Current De-rating

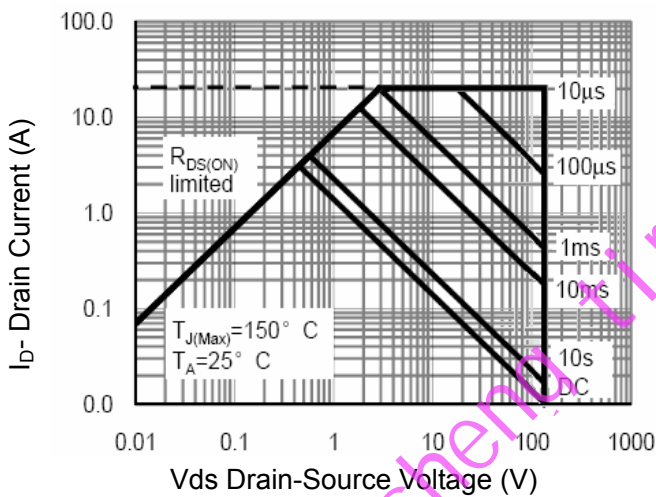


Figure 8 Safe Operation Area

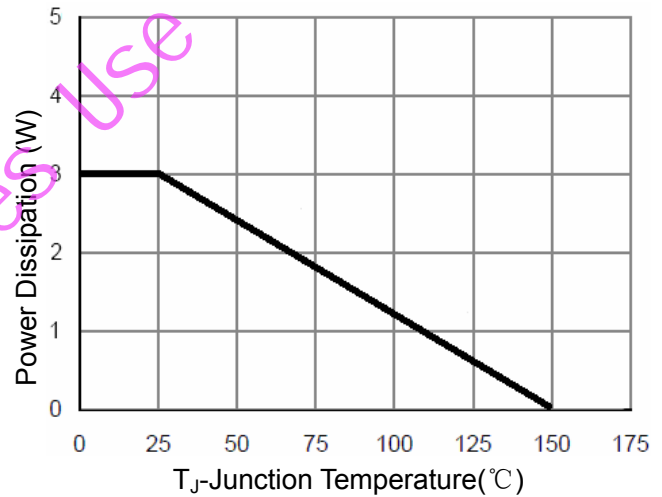


Figure 10 Power De-rating

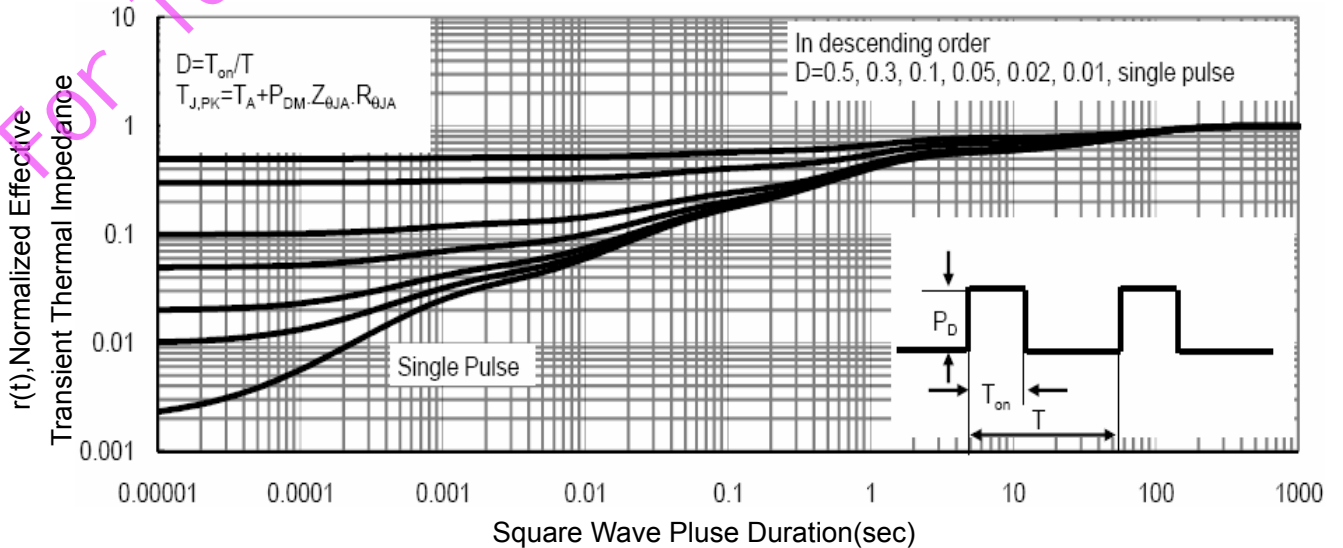
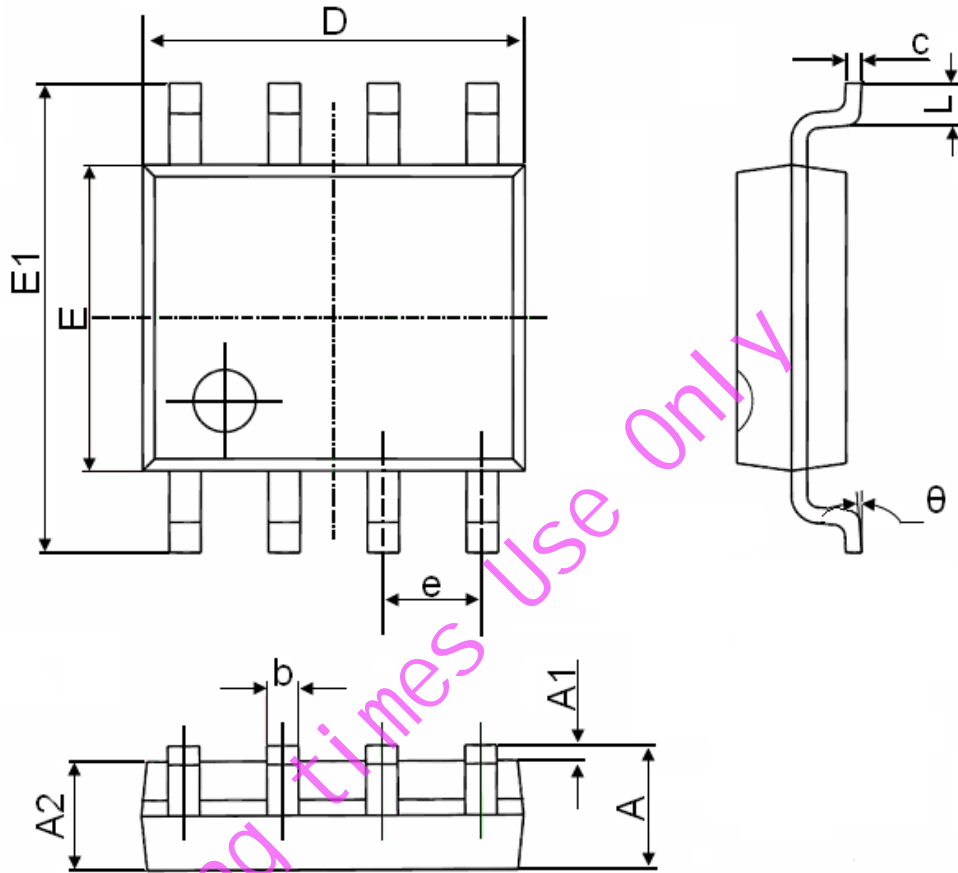


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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